

Supporting Information

Dynamic halide perovskite heterojunction generates direct current

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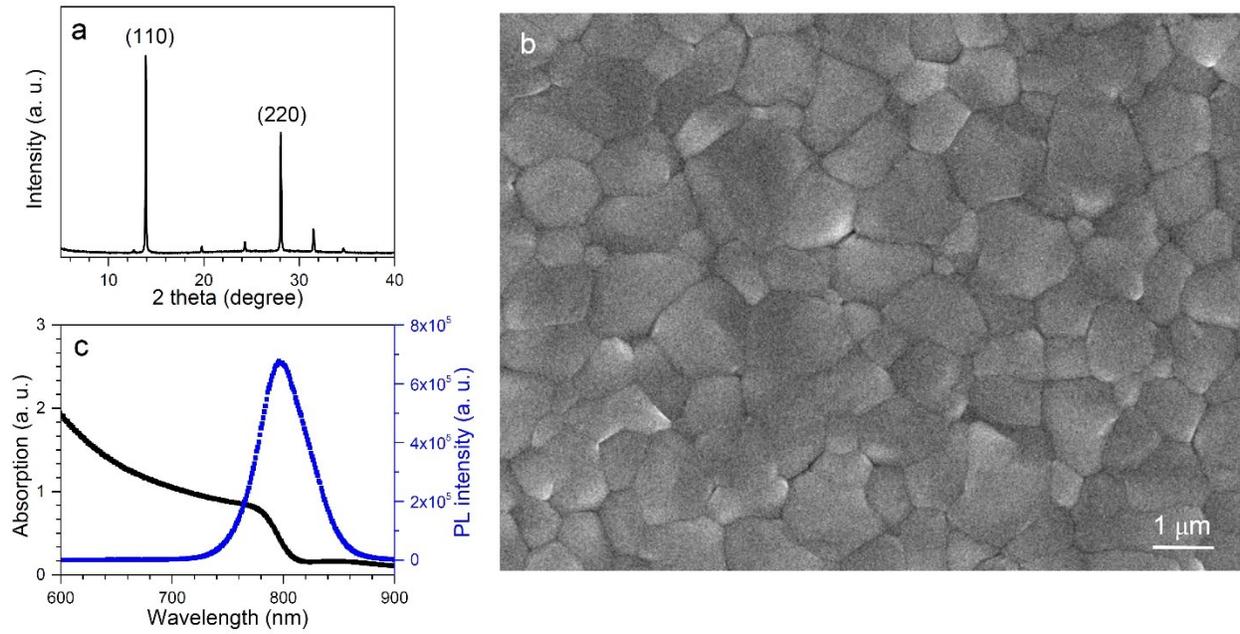


Figure S1. (a) XRD, (b) SEM, and (c) absorption and PL spectrum of FAPbI₃ perovskite film. XRD, PL, and absorption samples were prepared on glass substrates. The SEM sample was prepared on FTO conductive substrate.

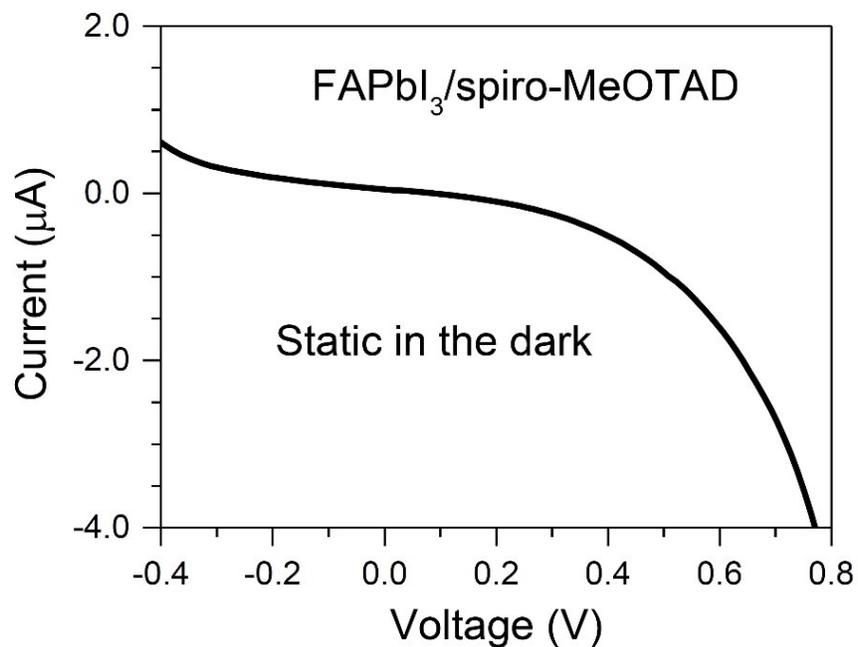


Figure S2. IV curve of the static FAPbI₃/Spiro heterojunction by pressing the spiro-coated electrode on the FAPbI₃-coated electrode.

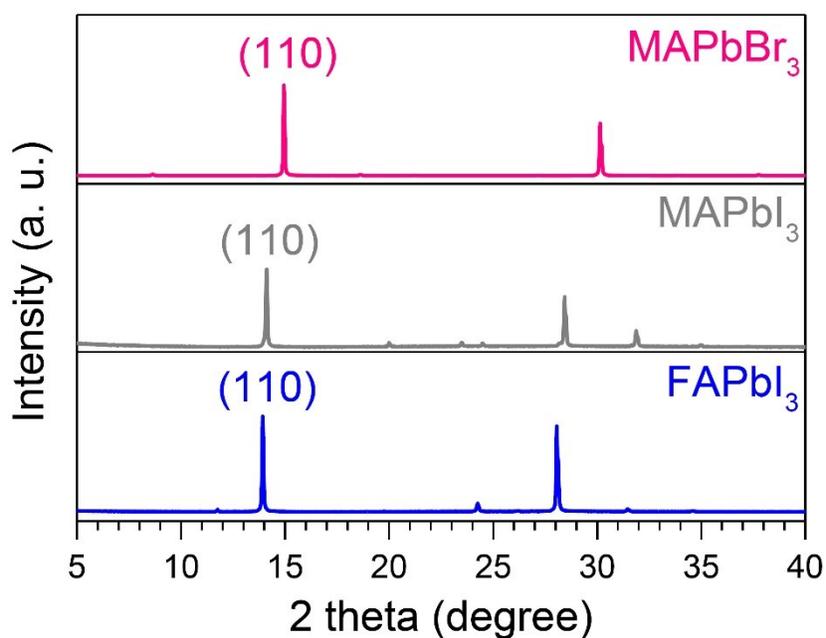


Figure S3. XRD results of FAPbI₃, MAPbI₃ and MAPbBr₃ films on glass substrate.

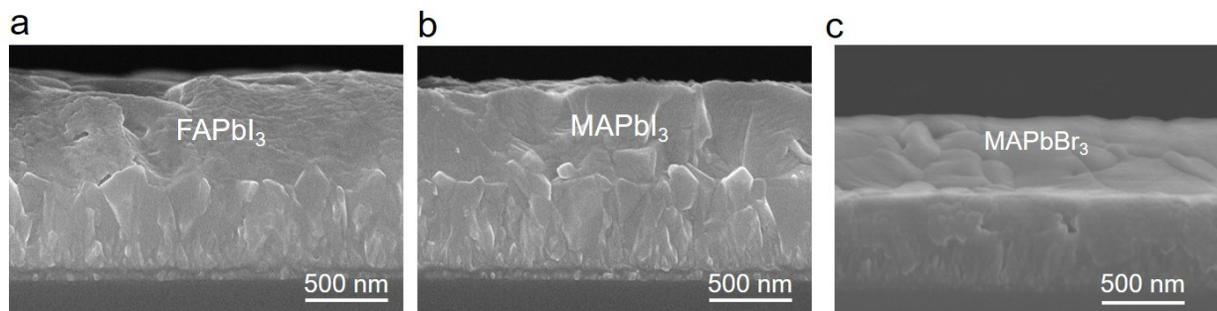


Figure S4. Cross-sectional SEM images of FAPbI₃, MAPbI₃ and MAPbBr₃ on FTO substrate.

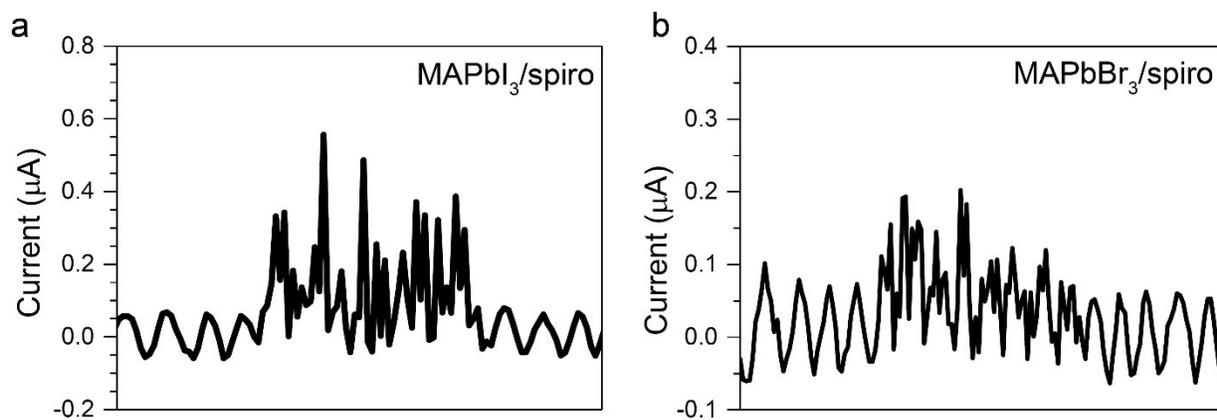


Figure S5. Current performance of (a) the MAPbI₃/spiro and (b) the MAPbBr₃/spiro heterojunction by pressing and sliding the spiro-coated electrode on the MAPbX₃ (X= I or Br)-coated electrode. The applied force was ~5 N and contact area was ~1 cm².

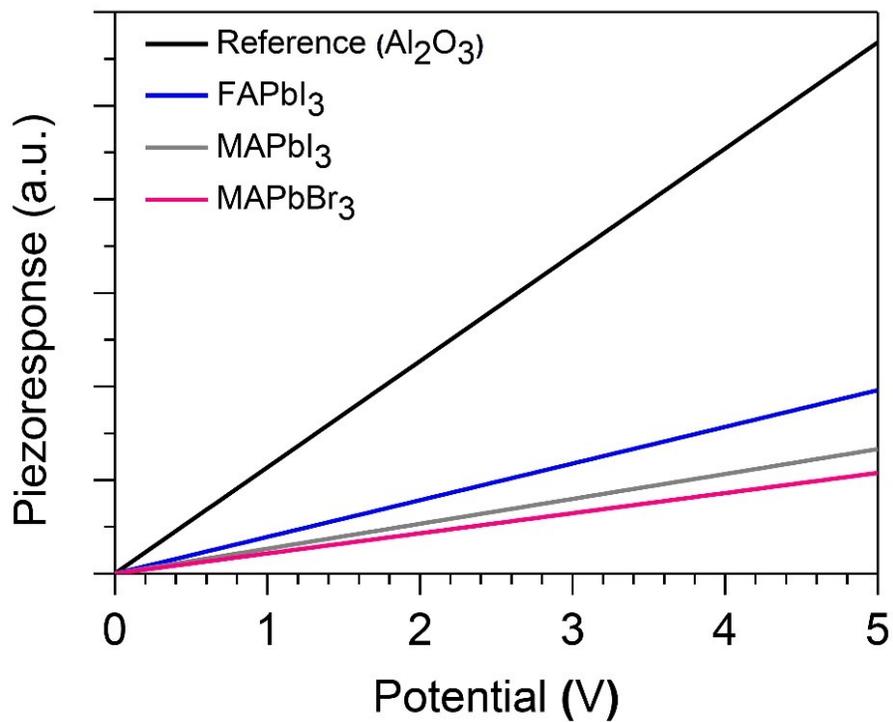


Figure S6. Piezoresponse of FAPbI₃, MAPbI₃ and MAPbBr₃. Al₂O₃ was measure as reference. These samples were prepared on FTO conductive substrate and piezoresponse in d₃₃ direction of each perovskite sample was measured by piezoresponse force microscopy (PFM).

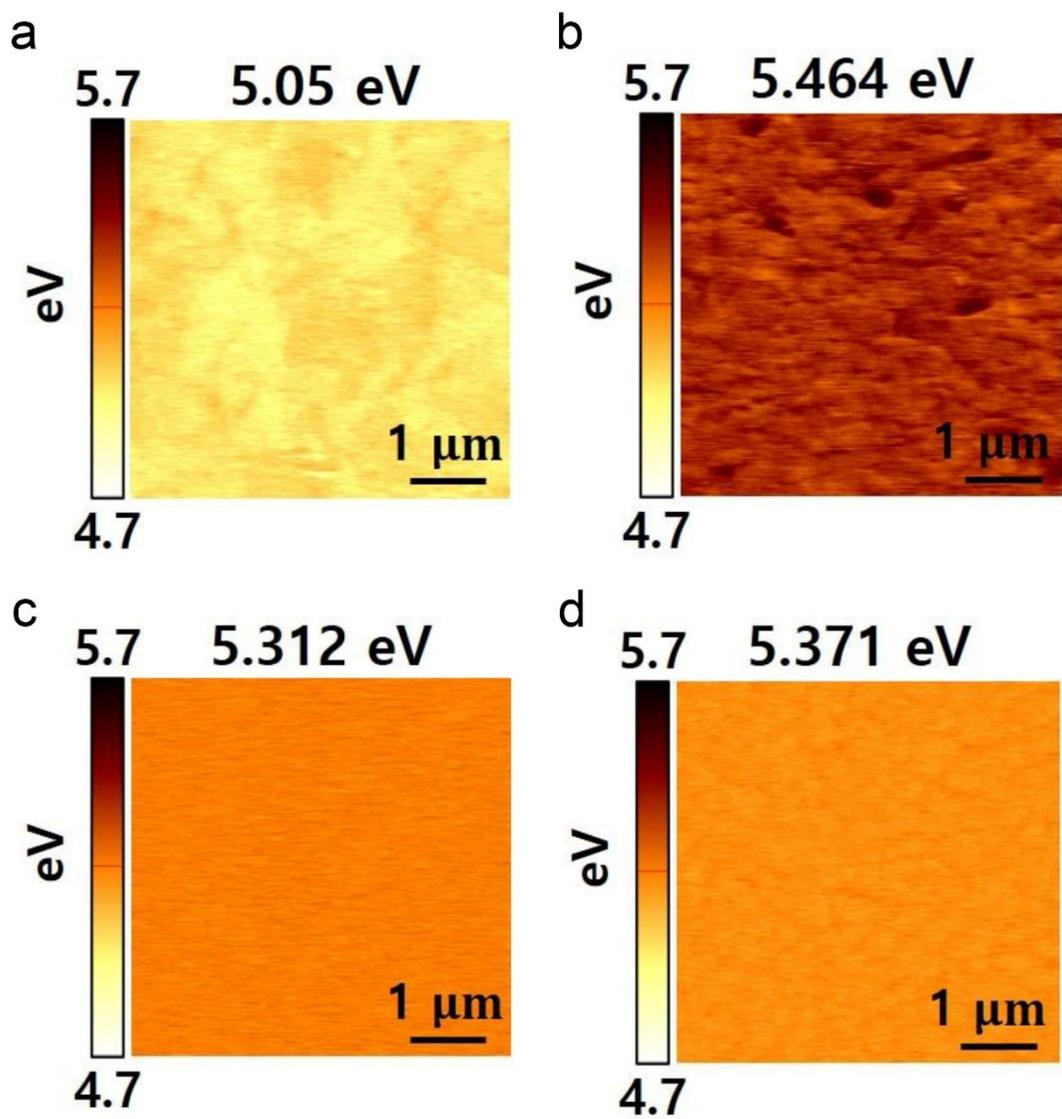


Figure S7. KPFM of (a) FAPbI₃, (b) MAPbI₃, (c) MAPbBr₃, and (d) spiro. These samples were prepared on FTO conductive substrate.

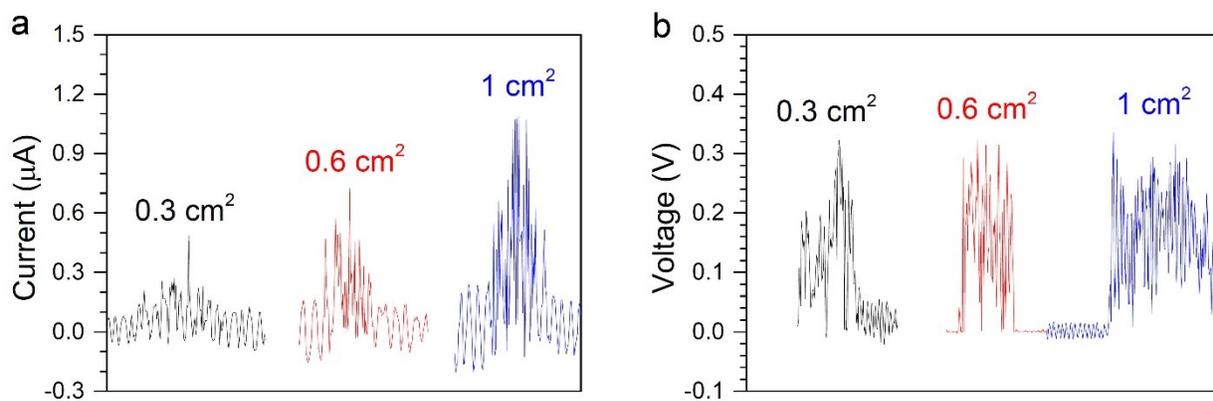


Figure S8. Current and voltage output change versus area on the dynamic $\text{FAPbI}_3/\text{spiro}$ heterojunction by pressing and sliding the spiro-coated electrode on the FAPbI_3 -coated electrode. The applied force is $\sim 5 \text{ N}$.

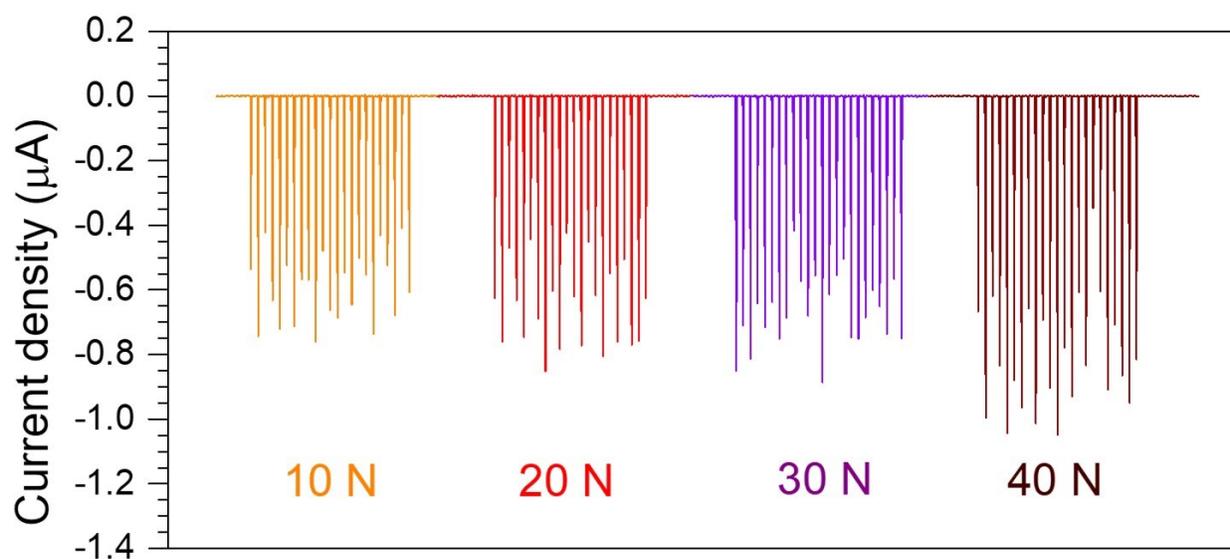


Figure S9. Dependence of current output on applied force on the dynamic $\text{FAPbI}_3/\text{spiro}$ heterojunction. The contact area was $\sim 0.5 \text{ cm}^2$.

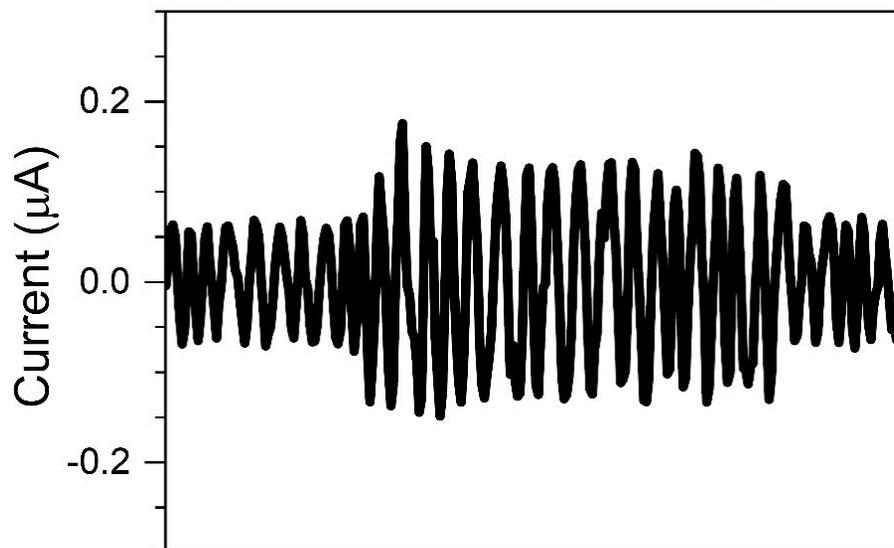


Figure S10. Current output performance of the PEA₂PbI₄/spiro heterojunction by pressing and sliding the spiro-coated electrode on the PEA₂PbI₄-coated electrode. The contact area is ~1 cm² and the applied force is ~5 N.

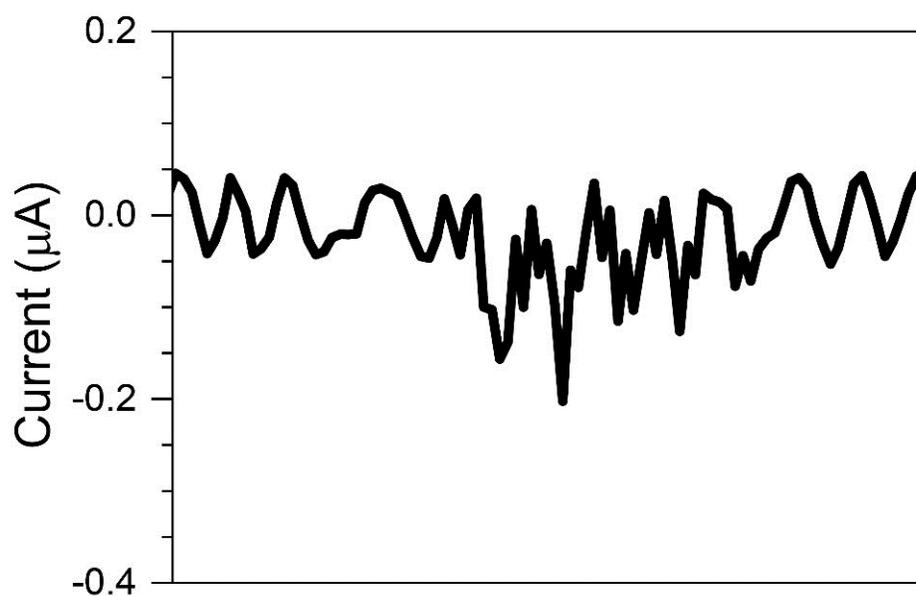


Figure S11. Current performance of the perovskite/TiO₂ heterojunction by pressing and sliding the TiO₂-coated electrode on the perovskite-coated electrode. The contact area is ~1 cm² and the applied force is ~5 N.

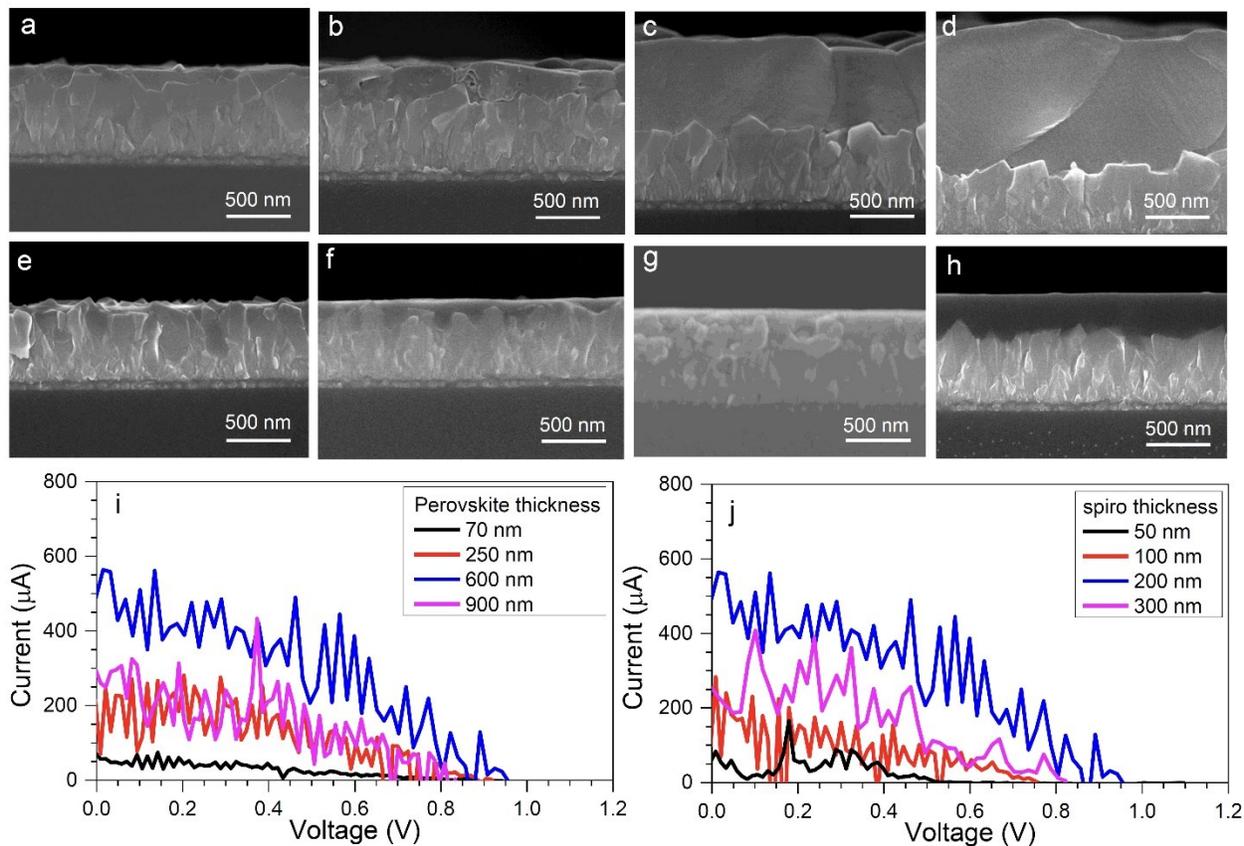


Figure S12. Influence of the thickness of perovskite film and spiro film on the triboelectric and photovoltaic coupling performance. Cross-sectional SEM images of perovskite films with thicknesses of (a) 70 nm, (b) 250 nm, (c) 600 nm, (d) 900 nm and spiro films with thicknesses of (e) 50 nm, (f) 100 nm, (g) 200 nm, (h) 300 nm. IV curves of the devices with different thicknesses of (i) perovskite films and (j) spiro films. The contact area was $\sim 1 \text{ cm}^2$ and the applied force was $\sim 5 \text{ N}$.

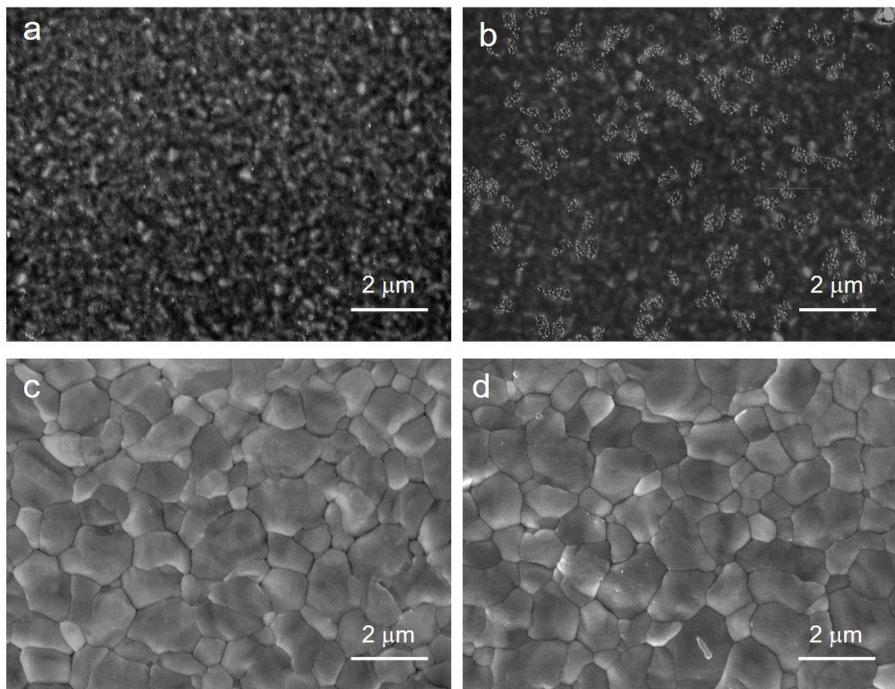


Figure S13. SEM images of (a, b) spiro and (c, d) perovskite films, where (a) and (c) are corresponding to the pristine spiro and perovskite films, respectively, and (b) and (d) for the spiro and perovskite films after 20 cycles under applied force of 40 N.

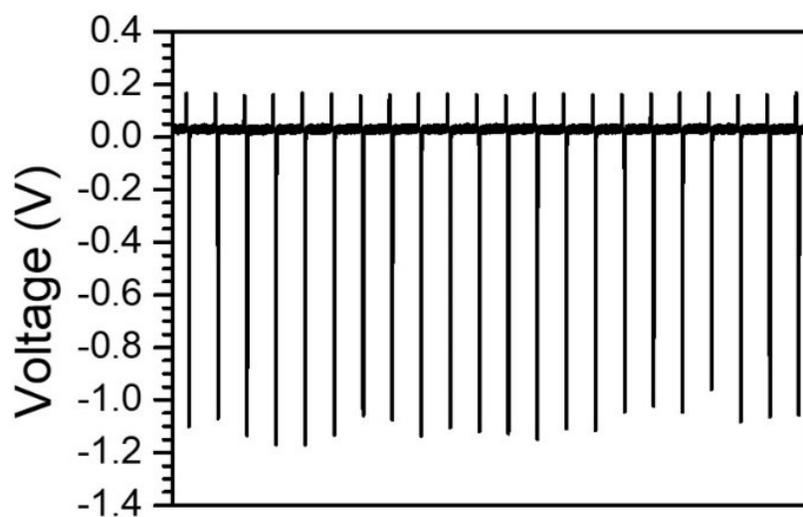


Figure S14. Voltage performance of the dynamic FAPbI₃/spiro heterojunction for 22 cycles under applied force of 40 N.

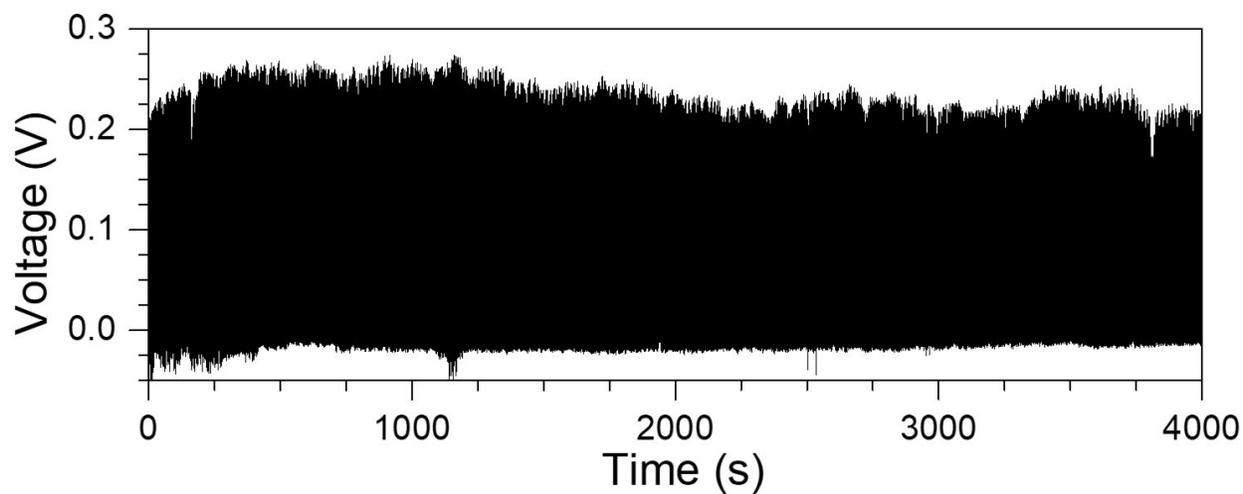


Figure S15. Voltage endurance performance of the dynamic FAPbI₃/spiro heterojunction under continuous sliding for 4000 s. The area was ~1 cm².

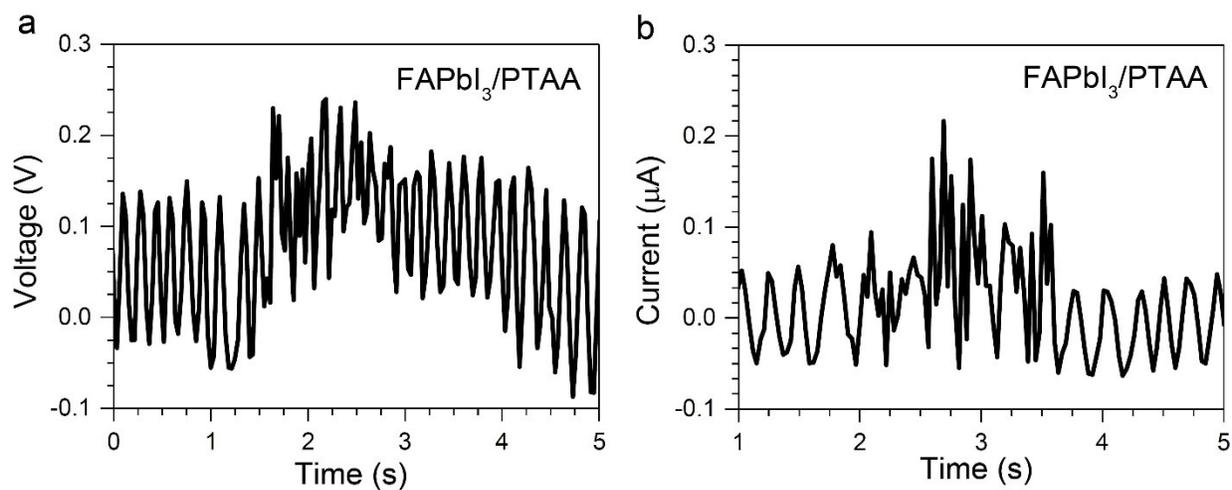


Figure S16. (a) Voltage and (b) current performance of the dynamic FAPbI₃/PTAA heterojunction by pressing and sliding the PTAA-coated electrode on the FAPbI₃-coated electrode. The applied force was ~5 N and the contact area was ~1 cm².

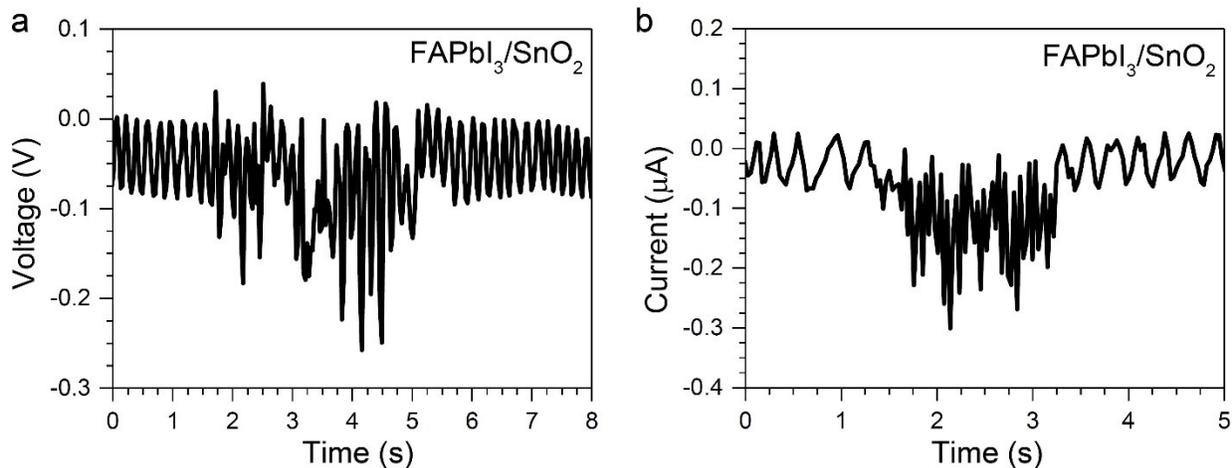


Figure S17. (a) Voltage and (b) current performance of the dynamic FAPbI₃/SnO₂ heterojunction by pressing and sliding the SnO₂-coated electrode on the FAPbI₃-coated electrode. The applied force was ~ 5 N and the contact area was ~ 1 cm².

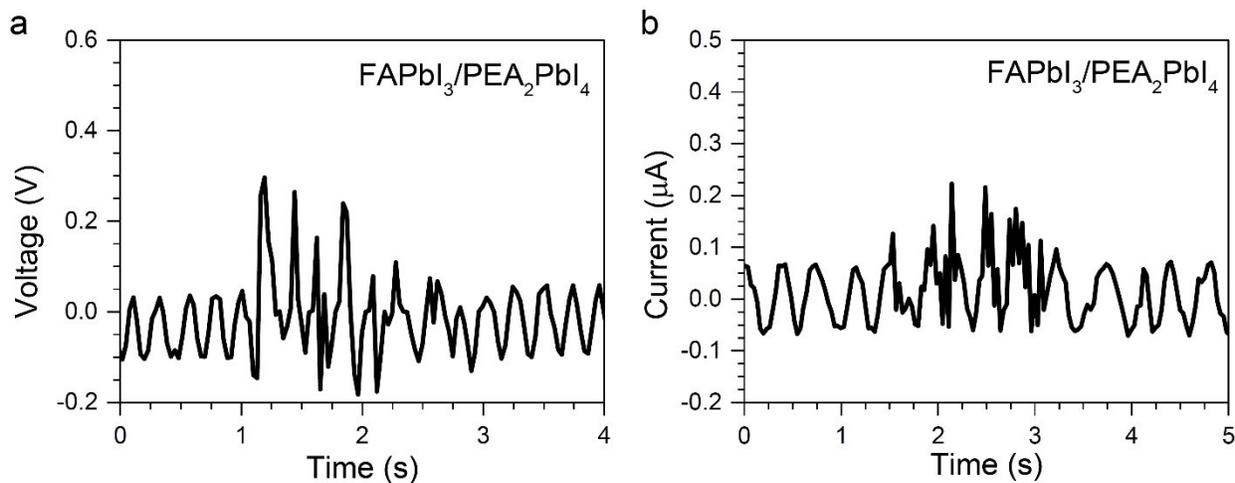


Figure S18. (a) Voltage and (b) current performance of the dynamic FAPbI₃/PEA₂PbI₄ heterojunction by pressing and sliding the PEA₂PbI₄-coated electrode on the FAPbI₃-coated electrode. The applied force is ~ 5 N and the contact area is ~ 1 cm².

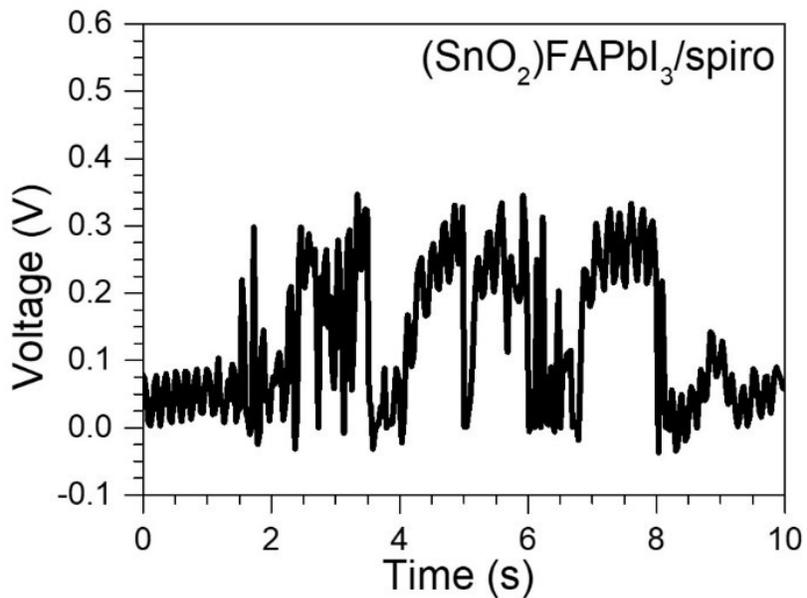


Figure S19. Voltage performance of the dynamic FAPbI₃/spiro heterojunction with SnO₂ as ETL under the perovskite film. The applied force is ~ 5 N and the contact area is ~ 1 cm².

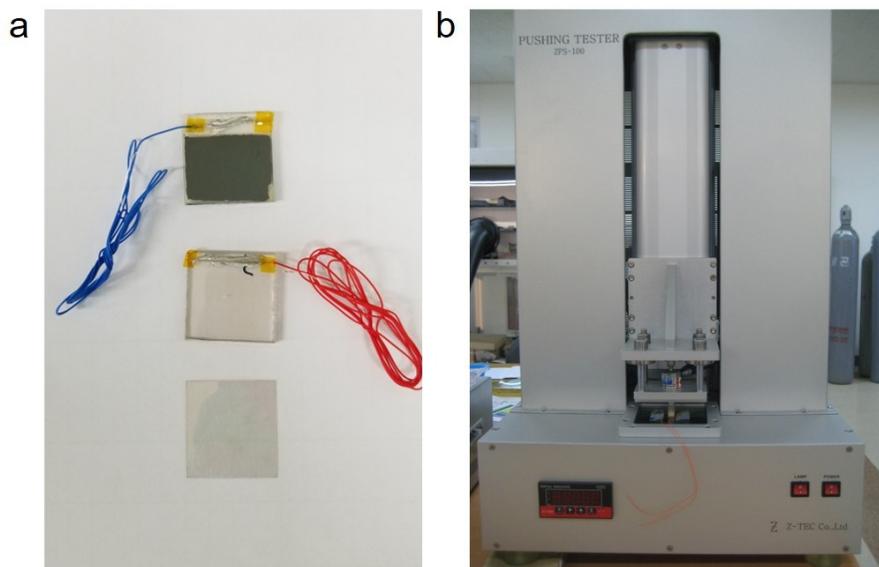


Figure S20. Digital photos of (a) the samples and (a) the setup for applying forces. Samples from up to down in (a) are FTO glass/perovskite, FTO glass/spiro, and PEN/ITO/spiro, respectively.